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<u>Set Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u> result set
side by side			
<u>DB=TDBD</u>	<u>PLUR=YES</u> ; <u>OP=OR</u>		
<u>L40</u>	<u>L39</u>	0	<u>L40</u>
<u>DB=DWPI</u>	<u>PLUR=YES</u> ; <u>OP=OR</u>		
<u>L39</u>	<u>L38</u>	0	<u>L39</u>
<u>DB=JPAB</u>	<u>PLUR=YES</u> ; <u>OP=OR</u>		
<u>L38</u>	<u>L37</u>	0	<u>L38</u>
<u>DB=EPAB</u>	<u>PLUR=YES</u> ; <u>OP=OR</u>		
<u>L37</u>	<u>L36</u>	0	<u>L37</u>
<u>DB=USOC</u>	<u>PLUR=YES</u> ; <u>OP=OR</u>		
<u>L36</u>	<u>L35</u>	0	<u>L36</u>
<u>DB=PGPB</u>	<u>PLUR=YES</u> ; <u>OP=OR</u>		
<u>L35</u>	<u>L34</u>	0	<u>L35</u>
<u>DB=USPT</u>	<u>PLUR=YES</u> ; <u>OP=OR</u>		
<u>L34</u>	<u>L32 same (graded or "nitrogen oncentration")</u>	0	<u>L34</u>

<u>L33</u>	L32 same graded or (nitrogen near7 (concentration))	12332	<u>L33</u>
<u>L32</u>	"gate dielectric" near7 (metal near3 nitride) <i>DB=TDDBD; PLUR=YES; OP=OR</i>	27	<u>L32</u>
<u>L31</u>	L30 <i>DB=DWPI; PLUR=YES; OP=OR</i>	0	<u>L31</u>
<u>L30</u>	L29 <i>DB=JPAB; PLUR=YES; OP=OR</i>	0	<u>L30</u>
<u>L29</u>	L28 <i>DB=EPAB; PLUR=YES; OP=OR</i>	0	<u>L29</u>
<u>L28</u>	L27 <i>DB=USOC; PLUR=YES; OP=OR</i>	0	<u>L28</u>
<u>L27</u>	L26 <i>DB=PGPB; PLUR=YES; OP=OR</i>	0	<u>L27</u>
<u>L26</u>	L25 <i>DB=USPT; PLUR=YES; OP=OR</i>	0	<u>L26</u>
<u>L25</u>	L22 and ("gate dielectric" near4 graded near5 nitrogen)	0	<u>L25</u>
<u>L24</u>	L22 and ("gate dielectric" near3 "nitrogen concentration")	0	<u>L24</u>
<u>L23</u>	L22 and "nitrogen concentration"	202	<u>L23</u>
<u>L22</u>	("gate dielectric" or "gate insulation") near5 ((nitrogen and metal) or (metal near2 oxy near2 nitride))	1966	<u>L22</u>
<u>L21</u>	("gate dielectric" or "gate insulation") near7 ((nitrogen and metal) or (metal near2 oxy near2 nitride))	2688	<u>L21</u>
<u>L20</u>	("gate dielectric" or "gate insulation") same ((nitrogen and metal) or (metal near2 oxy near2 nitride))	7755	<u>L20</u>
<u>L19</u>	6020243 <i>DB=PGPB; PLUR=YES; OP=OR</i>	45	<u>L19</u>
<u>L18</u>	L17 <i>DB=TDDBD; PLUR=YES; OP=OR</i>	0	<u>L18</u>
<u>L17</u>	L16 <i>DB=DWPI; PLUR=YES; OP=OR</i>	0	<u>L17</u>
<u>L16</u>	L15 <i>DB=JPAB; PLUR=YES; OP=OR</i>	0	<u>L16</u>
<u>L15</u>	L14 <i>DB=EPAB; PLUR=YES; OP=OR</i>	0	<u>L15</u>
<u>L14</u>	L13	0	<u>L14</u>
<u>L13</u>	L12 <i>DB=USPT; PLUR=YES; OP=OR</i>	0	<u>L13</u>
<u>L12</u>	L11 <i>DB=USOC; PLUR=YES; OP=OR</i>	0	<u>L12</u>
<u>L11</u>	L8 and capacitor	0	<u>L11</u>
<u>L10</u>	L9 <i>DB=USPT; PLUR=YES; OP=OR</i>	0	<u>L10</u>

<u>L9</u>	L8 and "first barrier metal"	0	<u>L9</u>
<u>L8</u>	L7 and fill	2	<u>L8</u>
<u>L7</u>	L6 and ((via\$ or feedthrough) near5 interlayer)	5	<u>L7</u>
<u>L6</u>	L5 and (interlayer near5 "etch stop")	9	<u>L6</u>
<u>L5</u>	L3 and ("etch stop" near5 (metal or conductor))	227	<u>L5</u>
<u>L4</u>	L3 and ("etch stop": near5 (metal or conductor))	227	<u>L4</u>
<u>L3</u>	L1 and ((metal or conductor) near4 insulat\$5)	23211	<u>L3</u>
<u>L2</u>	L1 and (metal near4 insulat\$5)	16944	<u>L2</u>
<u>L1</u>	(insulat\$5 near10 substrate)	82819	<u>L1</u>

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<u>DB=JPAB</u>	<u>PLUR=YES</u> ; <u>OP=OR</u>		
<u>L29</u>	<u>L28</u>	0	<u>L29</u>
<u>DB=EPAB</u>	<u>PLUR=YES</u> ; <u>OP=OR</u>		
<u>L28</u>	<u>L27</u>	0	<u>L28</u>
<u>DB=USOC</u>	<u>PLUR=YES</u> ; <u>OP=OR</u>		
<u>L27</u>	<u>L26</u>	0	<u>L27</u>
<u>DB=PGPB</u>	<u>PLUR=YES</u> ; <u>OP=OR</u>		
<u>L26</u>	<u>L25</u>	0	<u>L26</u>
<u>DB=USPT</u>	<u>PLUR=YES</u> ; <u>OP=OR</u>		
<u>L25</u>	<u>L22 and ("gate dielectric" near4 graded near5 nitrogen)</u>	0	<u>L25</u>

<u>L24</u>	L22 and ("gate dielectric" near3 "nitrogen concentration")	0	<u>L24</u>
<u>L23</u>	L22 and "nitrogen concentration"	202	<u>L23</u>
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<u>L19</u>	6020243 <i>DB=PGPB; PLUR=YES; OP=OR</i>	45	<u>L19</u>
<u>L18</u>	L17 <i>DB=TDBD; PLUR=YES; OP=OR</i>	0	<u>L18</u>
<u>L17</u>	L16 <i>DB=DWPI; PLUR=YES; OP=OR</i>	0	<u>L17</u>
<u>L16</u>	L15 <i>DB=JPAB; PLUR=YES; OP=OR</i>	0	<u>L16</u>
<u>L15</u>	L14 <i>DB=EPAB; PLUR=YES; OP=OR</i>	0	<u>L15</u>
<u>L14</u>	L13	0	<u>L14</u>
<u>L13</u>	L12 <i>DB=USPT; PLUR=YES; OP=OR</i>	0	<u>L13</u>
<u>L12</u>	L11 <i>DB=USOC; PLUR=YES; OP=OR</i>	0	<u>L12</u>
<u>L11</u>	L8 and capacitor	0	<u>L11</u>
<u>L10</u>	L9 <i>DB=USPT; PLUR=YES; OP=OR</i>	0	<u>L10</u>
<u>L9</u>	L8 and "first barrier metal"	0	<u>L9</u>
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